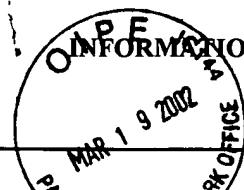


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## FOREIGN PATENT DOCUMENTS

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	02-244674	09/28/1990	JP			Part Eng

## OTHER DOCUMENT (Including Author, Title, Date, Pertinent Pages, Etc.)

Cu	"Table 22 Thermal/Thin Films Gate Etch and Doping Technology Requirement", p. 74, The National Technology Roadmap for Semiconductors Technology Needs
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